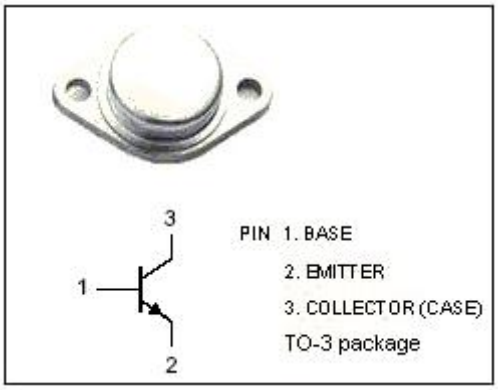
isc Silicon NPN Power Transistor 2SC3214

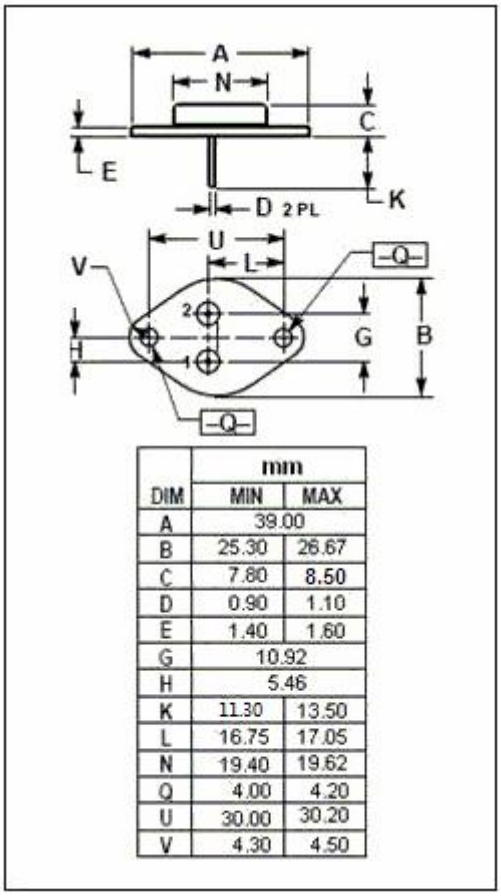


DESCRIPTION

- High Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= 800V (Min)
- High Switching Speed
- Large safe operating area
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for switching regulators,Motor controls,Ultrasonic Oscillators.



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	1200	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	5	A
P_C	Collector Power Dissipation @T_C=25℃	80	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-45~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustainig Voltage	I_C= 10mA; I_B=0	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 10mA; I_C= 0	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2.5A; I_B= 1.0A			2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 2.5A; I_B= 1.0A			1.5	V
h_{FE-1}	DC Current Gain	I_C= 1.0A; V_{CE}= 5V		20		
I_{CBO}	Collector Cutoff Current	V_{CB}= 1200V; I_E= 0			0.1	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 800V; R_{BE}= ∞			0.1	mA